

ABSTRACT

Provides an IC chip for high frequency region, particularly, packaged substrate in which no malfunction or
5 error occurs even if 3 GHz is exceeded.

A conductive layer 34P is formed in the thickness of 30 μm on a core substrate 30 and a conductive circuit 58 on an interlayer resin insulation layer 50 is formed in the thickness of 15 μm . By thickening the conductive layer 34P, the volume of the
10 conductor itself can be increased thereby decreasing its resistance. Further, by using the conductive layer 34 as a power source layer, the capacity of supply of power to an IC chip can be improved.